

NPN Silicon RF Transistors

BF 457

BF 458

BF 459

SIEMENS AKTIENGESELLSCHAFT

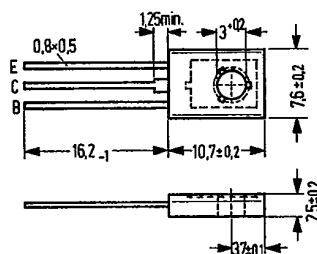
25C 04495

D—

for video and AF output stages

BF 457, BF 458 and BF 459 are epitaxial NPN silicon planar transistors in TO 126 plastic package (12 A 3 DIN 41 869). The collector is conductively connected to the metallic mounting area of the transistor. The transistors are especially designed for use in video output stages of TV receivers, for AF output stages of high operating voltage, and as driver transistors in horizontal deflection circuits.

Type	Ordering code
BF 457	Q62702-F315
BF 458	Q62702-F316
BF 459	Q62702-F317
Mica washer	Q62902-B62
Spring washer	Q62902-B63
A 3 DIN 137	



Approx. weight 0.5 g Dimensions in mm

Maximum ratings

	BF 457	BF 458	BF 459	
Collector-base voltage	160	270	300	V
Collector-emitter voltage	160	250	300	V
Emitter-base voltage	5	5	5	V
Collector current	100	100	100	mA
Base current	50	50	50	mA
Collector peak current	300	300	300	mA
Junction temperature	150	150	150	°C
Storage temperature range		-55 to +150		°C
Total power dissipation ($T_{amb} \leq 25^\circ\text{C}$)	1.2	1.2	1.2	W
($T_{case} \leq 45^\circ\text{C}$)	10	10	10	W

Thermal resistance

Junction to ambient air	R_{thJA}	≤ 104	≤ 104	≤ 104	K/W
Junction to case	R_{thJC} ¹⁾	≤ 10	≤ 10	≤ 10	K/W

1) Starting torque for the M3 screw used for mounting = max. 0.8 Nm. Thermal resistance of a 50 μ mica washer, ungreased 8 K/W; greased 4 K/W. A washer or corrugated spring washer A 3 DIN 137 should be placed below the screw head.

SIEMENS AKTIENGESSELLSCHAF

Static characteristics ($T_{amb} = 25^{\circ}\text{C}$)

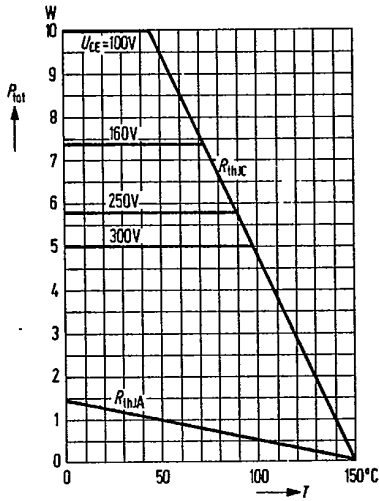
		BF 457	BF 458	BF 459	
Collector-base breakdown voltage ($I_C = 100 \mu\text{A}$)	$V_{(BR)CBO}$	> 160	> 250	> 300	V
Collector-emitter breakdown voltage ($I_C = 10 \text{ mA}$)	$V_{(BR)CEO}$	> 160	> 250	> 300	V
Emitter-base breakdown voltage ($I_E = 100 \mu\text{A}$)	$V_{(BR)EBO}$	> 5	> 5	> 5	V
Collector cutoff current ($V_{CB} = 100 \text{ V}$)	I_{CBO}	< 50	—	—	nA
($V_{CB} = 200 \text{ V}$)	I_{CBO}	—	< 50	—	nA
($V_{CB} = 250 \text{ V}$)	I_{CBO}	—	—	< 50	nA
Emitter cutoff current ($V_{EB} = 3 \text{ V}$)	I_{EBO}	< 50	< 50	< 50	nA
Collector-emitter saturation voltage ($I_C = 30 \text{ mA}$; $I_B = 6 \text{ mA}$)	V_{CEsat}	< 1	< 1	< 1	V
DC current gain ($I_C = 30 \text{ mA}$; $V_{CE} = 10 \text{ V}$)	h_{FE}	> 25	> 25	> 25	—

Dynamic characteristics ($T_{amb} = 25^{\circ}\text{C}$)

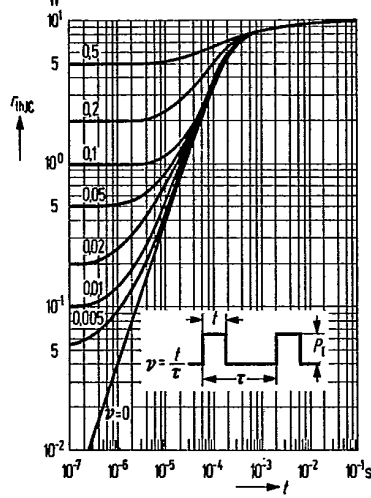
Transition frequency ($V_{CE} = 10 \text{ V}$; $I_C = 15 \text{ mA}$; $f = 20 \text{ MHz}$)	f_T	90	90	90	MHz
Reverse transfer capacitance ($V_{CE} = 30 \text{ V}$; $f = 1 \text{ MHz}$; $I_C = 1 \text{ mA}$)	$-C_{12e}$	4.2	4.2	4.2	pF
Output capacitance ($V_{CB} = 30 \text{ V}$; $f = 1 \text{ MHz}$; $I_E = 0$)	C_{22e}	5.5	5.5	5.5	pF

SIEMENS AKTIENGESELLSCHAFT

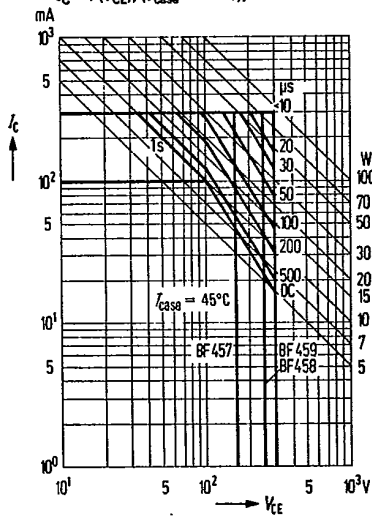
Total perm. power dissipation
versus temperature
 $P_{tot} = f(T)$



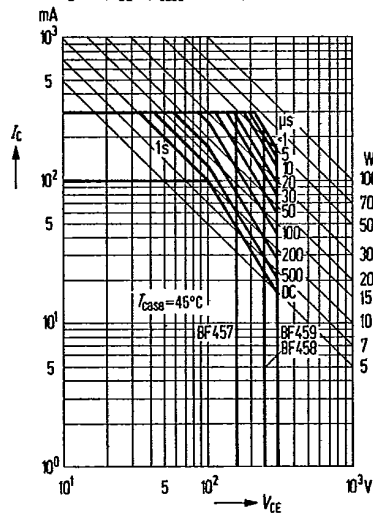
Permissible pulse load
 $r_{thJC} = f(t)$; $v = \text{parameter}$



Permissible operating range
 $I_C = f(V_{CE})$; ($T_{case} = 45^\circ\text{C}$); $v = 0.01$

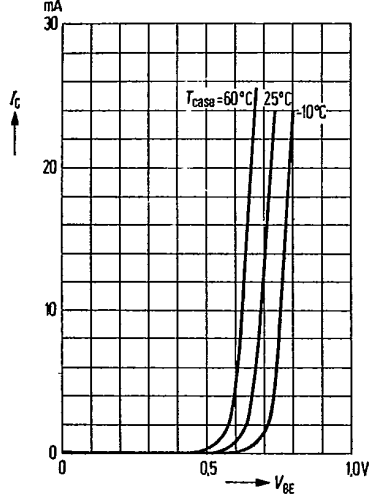


Permissible operating range
 $I_C = f(V_{CE})$; ($T_{case} = 45^\circ\text{C}$); $v = 0.1$

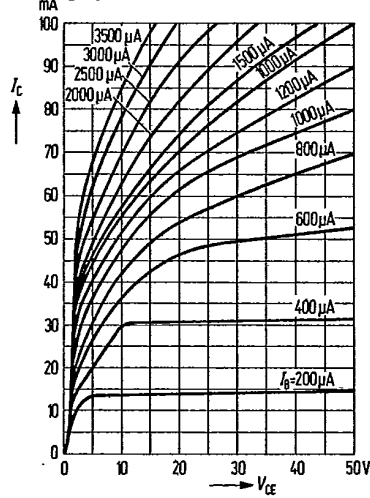


SIEMENS AKTIENGESSELLSCHAF

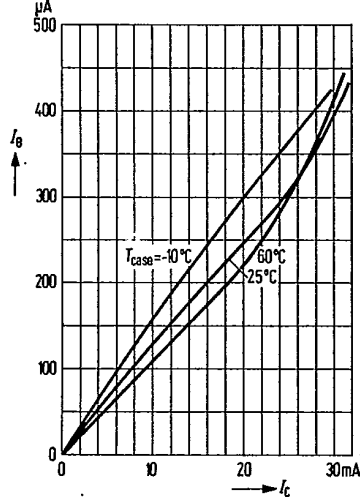
Collector current $I_C = f(V_{BE})$
 $V_{CE} = 10 \text{ V}; T_{case} = \text{parameter}$



Output characteristics $I_C = f(V_{CE})$
 $I_B = \text{parameter}$



Base current $I_B = f(I_C)$
 $V_{CE} = 10 \text{ V}; T_{case} = \text{parameter}$



Transition frequency $f_T = f(I_C)$
 $V_{CE} = 10 \text{ V}; f = 20 \text{ MHz}$

